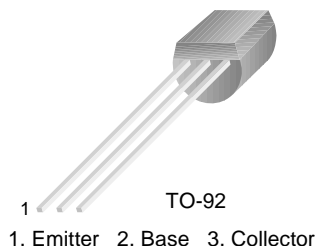


2N6515

2N6515

High Voltage Transistor

- Collector-Emitter Voltage: $V_{CE0} = 250V$
- Collector Dissipation: $P_C (max) = 625mW$
- Complement to 2N6518



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ C$

Electrical Characteristics $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	* Collector-Emitter Breakdown Voltage	$I_C = 1mA, I_B = 0$	250			V
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	250			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 150V, I_E = 0$			50	nA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = 5V, I_C = 0$			50	nA
h_{FE}	* DC Current Gain	$I_C = 1mA, V_{CE} = 10V$ $I_C = 10mA, V_{CE} = 10V$ $I_C = 30mA, V_{CE} = 10V$ $I_C = 50mA, V_{CE} = 10V$ $I_C = 100mA, V_{CE} = 10V$	35 50 50 45 25		300 220	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10mA, I_B = 1mA$ $I_C = 20mA, I_B = 2mA$ $I_C = 30mA, I_B = 3mA$ $I_C = 50mA, I_B = 5mA$			0.3 0.35 0.5 1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10mA, I_B = 1mA$ $I_C = 20mA, I_B = 2mA$ $I_C = 30mA, I_B = 3mA$			0.75 0.85 0.9	V
C_{ob}	Output Capacitance	$V_{CB} = 20V, I_E = 0, f = 1MHz$			6	pF
f_T	Current Gain Bandwidth Product	$I_C = 10mA, V_{CE} = 20V, f = 20MHz$	40		200	MHz
$V_{BE(on)}$	Base Emitter On Voltage	$I_C = 100mA, V_{CE} = 10V$			2	V

* Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Characteristics

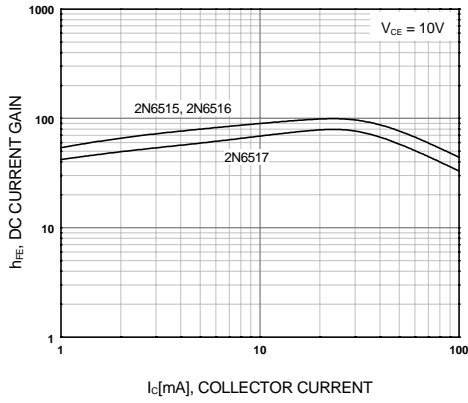


Figure 1. DC current Gain

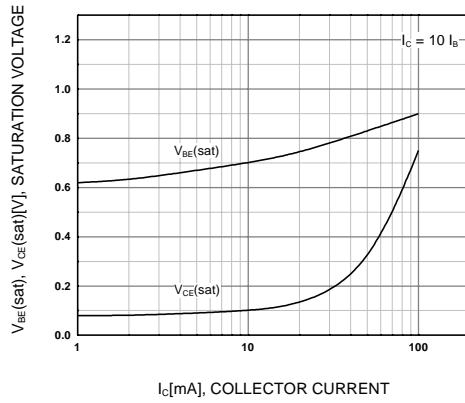


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

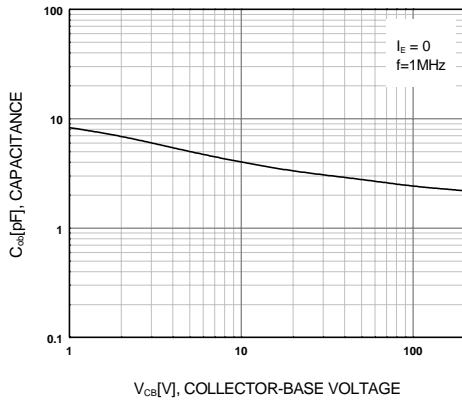


Figure 3. Collector-Base Capacitance

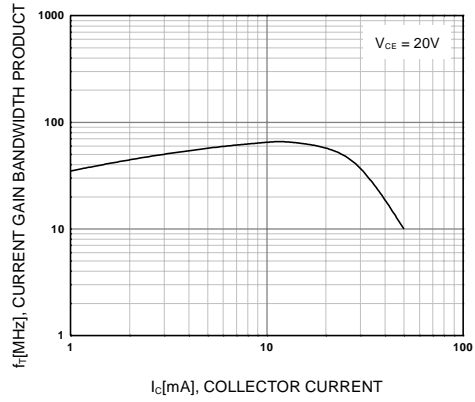
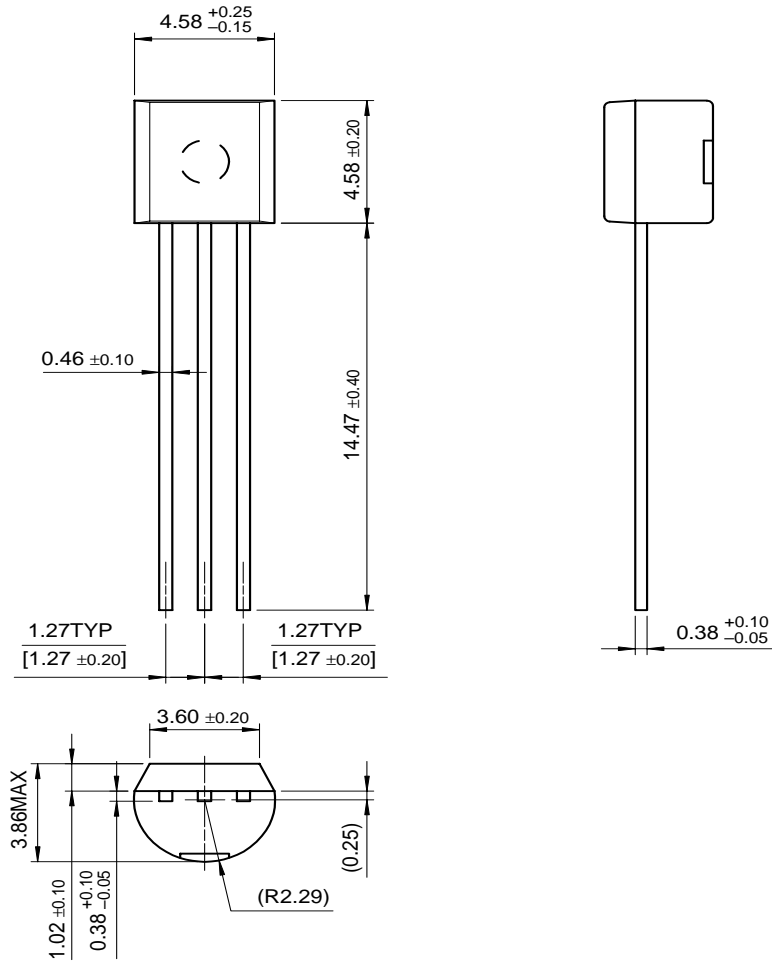


Figure 4. Current Gain Bandwidth Product

Package Dimensions

2N6515

TO-92



Dimensions in Millimeters

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